

**IMEP-LAHC, UMR 5130**

**Equipe CMNE "Composants Micro-Nanoélectroniques"**

**Publications dans des conférences internationales avec actes (2009)**

Année	Auteurs	Titre		Sigle	Conférence	Lieu, date	Actes
2009	N. Rodriguez, F. Gámiz, S. Cristoloveanu	Characterization, modelling and simulation of Sub-45nm SOI devices		CAS	International Semiconductor Conference (CAS'2009), 12-14 Oct., 2009, Sinaia (RO)	Sinaia, Romania (12-14 Oct. 2009)	IEEE Conference Proceedings CFP 09CAS-PRT, ISBN 978-1-4244-4413-7, Volume 1, pp. 57-63 (2009)
2009	B. Bercu, L. Montès, F. Rochette, M. Mouis, X. Xin, P. Morfouli	High mechanical stress applied to FD-SOI transistors using ultra thin Silicon membranes		CAS	International Semiconductor Conference (CAS'2009), 12-14 Oct., 2009, Sinaia (RO)	Sinaia, Romania (12-14 Oct. 2009)	IEEE Conference Proceedings CFP 09CAS-PRT, ISBN 978-1-4244-4413-7, Volume 1, pp. 93-96 (2009)
2009	F. Balestra	SOI - a platform for transition from micro to nano	Invited paper	CAS	International Semiconductor Conference (CAS'2009), 12-14 Oct., 2009, Sinaia (RO)	Sinaia, Romania (12-14 Oct. 2009)	IEEE Conference Proceedings CFP 09CAS-PRT, ISBN 978-1-4244-4413-7, Volume 1, pp. 3-12 (2009)
2009	F. Balestra	SOI, a platform for transition from micro to nano	Invited paper	CAS	IEEE International Semiconductor Conference (CAS)	Sinaia, Romania, Oct. 2009	CAS 2009 Proceedings, IEEE, to be published
2009	Y. Bae, K-I. Na, S. Cristoloveanu, W. Xiong, C.R. Cleavelin, J-H. Lee	Special effects in triple gate MOSFETs fabricated on silicon-on-insulator (SOI)		CAS	International Semiconductor Conference (CAS'2009), 12-14 Oct., 2009, Sinaia (RO)	Sinaia, Romania (12-14 Oct. 2009)	IEEE Conference Proceedings CFP 09CAS-PRT, ISBN 978-1-4244-4413-7, Volume 1, pp. 51-56 (2009)
2009	F. Domengie, J.L. Regolini, D. Bauza	Study of Metal Contamination in CMOS Image Sensors by Dark Current and Deep Level Transient Spectroscopies		DRIP	13th International Conference on Defects - Recognition, Imaging and Physics in Semiconductors (DRIP XIII)	Wheeling, USA (13-17 September 2009)	Abstract booklet. Extended papers submitted to J. Electron. Materials
2009	F. Balestra	Multi-gate Devices for High Performance, Ultra Low Power and Memory applications	Invited paper	ECS	ECS Int. Symposium "ULSI Process Integration"	Vienna, Austria (Oct. 2009)	to be published in ECS Proceedings
2009	F. Ducroquet, E. Rauwel, C. Dubourdieu	Flat-band voltage and structural properties of Hafnium Dioxide grown by liquid-injection MOCVD		ECS Fall Meeting	216th ECS Meeting - 7th symp. on high dielectric constant materials and gate stacks - Symp E4, #2018	Vienna, Austria (4-9 october 2009)	ECS Transactions, Vol. 25, no.6, pp. 23-31 (2009)
2009	D. Bauza, O. Ghobar, N. Guenifi, and S. Bayon	Advanced analysis of silicon interface traps in MOSFET's with SiO <sub>2</sub> and HfO <sub>2</sub> as gate dielectrics	Invited paper	ECS Spring Meeting	215th Meeting of the Electrochemical Soc., 10th Symposium on Silicon Nitride, Silicon Dioxide, and Alternate Emerging Dielectrics	San Francisco (USA), May 24-29 2009	ECS Transactions, Vol. 19, n°2, pp. 19-54 (2009), ISBN: 978-1-56677-710-0.
2009	K-Y. Na, S. Cristoloveanu, Y-H. Bae, W. Xiong, C.R. Cleavelin, P. Patruno, J-H. Lee	Comparison of short channel effect between SOI and sSOI triple-gate MOSFETs.		ECS Spring Meeting	215th Meeting of the Electrochemical Soc., 14th Int. Symposium on Silicon on Insulator Technology and Devices	San Francisco, USA (25-29 May 2009)	Proc. in Silicon-on-Insulator Technology and Devices 14, (Y. Omura, S. Cristoloveanu, F. Gamiz, B-Y. Nguyen eds.), Pennington (USA), ECS Transactions, in press (2009)

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2009	M. Bawedin, S. Cristoloveanu, D. Flandre, F. Udrea	Floating-Body Memory: Concepts, Physics and Challenges.	Invited paper	ECS Spring Meeting	215th Meeting of the Electrochemical Soc., 14th Int. Symposium on Silicon on Insulator Technology and Devices	San Francisco, USA (25-29 May 2009)	Proc. in Silicon-on-Insulator Technology and Devices 14, (Y. Omura, S. Cristoloveanu, F. Gamiz, B-Y. Nguyen eds.), Pennington (USA), ECS Transactions, in press (2009)
2009	C. Dubourdieu, O. Salicio, F. Ducroquet, I. Matko, D. Daniele	High k SrTiO3 perovskite on Si/SiO2: CVD growth interface engineering and dielectric properties	Invited paper	ECS Spring Meeting	215th ECS Meeting, 10th Symposium on Silicon Nitride, Silicon Dioxide, and Alternate Emerging Dielectrics, Symp E5. #833	San Francisco (USA) , 24-29 mai 2009	ECS Transactions, Vol. 19, n°2, pp. 669-684 (2009), ISBN: 978-1-56677-710-0.
2009	W. Van Den Daele, E. Augendre, S. Cristoloveanu, C. Le Royer, L. Clavelier, J-F. Damlencourt, E. Guiot	Low-temperature measurements on Germanium-on-Insulator pMOSFETs: evaluation of the background doping level		ECS Spring Meeting	215th Meeting of the Electrochemical Soc., 14th Int. Symposium on Silicon on Insulator Technology and Devices	San Francisco, USA (25-29 May 2009)	Proc. in Silicon-on-Insulator Technology and Devices 14, (Y. Omura, S. Cristoloveanu, F. Gamiz, B-Y. Nguyen eds.), Pennington (USA), ECS Transactions, in press (2009)
2009	F. Balestra	SOI as a platform for transition from micro to nano	Invited paper	ECS Spring Meeting	215th ECS Meeting, Symposium E9, 14th Symposium on SOI Devices and Technology	San Francisco, USA (May 24-29, 2009 )	ECS Transactions, to be published
2009	C. Dubourdieu, E. Rauwel, Y. Lai, O. Salicio, A. Klein, O. Lebedev, G. Van Tendeloo, F. Ducroquet, S. Rushworth	Synthesis by CVD and characterisation of nanoscale functional films and 1D structures	Invited paper	E-MRS	E-MRS Spring Meeting, 2e symp. on Synthesis, processing and characterization of nanoscale multi-functional oxide films	Strasbourg, France (8-12 June 2009)	Conference workbook, symp H2.1
2009	M.A. Exarchos, G.J. Papaioannou, J.Jomaah, F. Balestra	Investigation of defects introduced by static and dynamic hot carrier stress on SOI partiallydepleted body-contact MOSFETs		ESREF	European Sympoium on Reliability of Electron Devices, Failure Physics and Analysis (ESREF)	Arcachon (Oct. 2009)	
2009	E. Buccafurri, A. Medjahdi, F. Calmon, R. Clerc, M. Pala, A. Poncet, G. Ghibaudo	Challenges and Prospects of RF Oscillators Using Silicon Resonant Tunneling Diodes		ESSDERC	European Solid-State Device Research Conference	Athens, Greece (14-18 Sept 2009)	Proceeding of ESSDERC, IEEE pp. 237-241
2009	J. Antoszewski, J.M. Dell, L. Faraone, S. Cristoloveanu, N. Bresson	Electron magnetoresistance mobility in silicon on insulator layers using Kelvin's technique		ESSDERC	European Solid-State Device Research Conference	Athens, Greece (14-18 Sept 2009)	Proceeding of ESSDERC, IEEE pp. 300-302
2009	J. Coignus, C. Leroux, R. Clerc, G. Ghibaudo, G. Reibold and F. Boulanger	Experimental Investigation of Transport Mechanisms through HfO2 Gate Stacks in nMOS Transistors		ESSDERC	European Solid-State Device Research Conference	Athens, Greece (14-18 Sept 2009)	Proceeding of ESSDERC, IEEE pp. 169-173

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2009	G. Bidal, J.L. Huguenin, S. Denorme, D. Fleury, N. Loubet, A. Pouydebasque, P. Perreau, F. Leverd, S. Barnola, R. Beneyton, B. Orlando, P. Gouraud, T. Salvetat, L. Clement, S. Monfray, G.Ghibaud, F. Boeuf and T. Skotnicki	Gate-All-Around technology: taking advantage of ballistic transport?		ESSDERC	39th European Solid-State Device Research Conference (ESSDERC'09)	Athens, Greece (14-18 Sept 2009)	
2009	Diana Lopez, Cédric Leyris, Stéphane Ricq, Francis Balestra	Noise as a characterization tool for reliability under illumination of transfer gate transistor for image sensors applications		ESSDERC	39th European Solid-State Device Research Conference (ESSDERC'09)	Athens, Greece (14-18 Sept 2009)	
2009	L. Gerrer, G. Ghibaud, G. Ribes	Oxide Soft BreakDown : From Device Modeling to Small Circuit Simulation.		ESSDERC	39th European Solid-State Circuit Research Conference (ESSDERC'09)	Athens, Greece (14-18 Sept 2009)	
2009	W. Van Den Daele, S. Cristoloveanu, E. Augendre, C. Le Royer, L. Clavelier, J-F. Damlencourt	Advanced pMOSFET on germanium-on-insulator : low temperature properties.		Euro-SOI	5th EUROSIOI Workshop	Göteborg, Sweden (19-21Jan. 2009)	Abstract booklet
2009	M. Bawedin, S. Cristoloveanu, F. Udrea, D. Flandre	Dynamic body potential variation in SOI MOSFETs: physics, model and applications.		Euro-SOI	5th EUROSIOI Workshop	Göteborg, Sweden (19-21Jan. 2009)	Abstract booklet
2009	K. Tachi, T. Ernst, C. Dupre, A. Hubert, S. Becu, H. Iwai, S. Cristoloveanu, O. Faynot	F-FET: electrostatics and influence of spacer thickness.		Euro-SOI	5th EUROSIOI Workshop	Göteborg, Sweden (19-21Jan. 2009)	Abstract booklet
2009	L. Pham-Nguyen, C. Fenouillet-Beranger, G. Ghibaud, T.Skotnicki, S. Cristoloveanu	Mobility enhancement by CESL strain in SOI MOSFETs.		Euro-SOI	5th EUROSIOI Workshop	Göteborg, Sweden (19-21Jan. 2009)	Abstract booklet
2009	N. Rodriguez, S. Cristoloveanu, F. Gamiz	Three-interface pseudo-MOSFET model : application to ultrathin BOX SOI wafers.		Euro-SOI	5th EUROSIOI Workshop	Göteborg, Sweden (19-21Jan. 2009)	Abstract booklet
2009	S. Cristoloveanu, J-P. Colinge, J. Fossum, C. Claeys, F. Balestra, O. Faynot, S. Monfray	What is the killing advantage of multiple-gate SOI MOSFETs: electrostatics and scalability, transport or functionality ?	Invited paper, panel session	Euro-SOI	5th EUROSIOI Workshop	Göteborg, Sweden (19-21Jan. 2009)	Abstract booklet

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2009	F. Balestra	Silicon-based devices and materials for nanoscale CMOS and beyond-CMOS	Invited paper	FTM	6th Advanced Research Workshop "Future Trends in Microelectronics: Unmapped Roads"	Sardinia, Italy (14-19 June 2009)	Future Trends in Microelectronics: Unmapped Roads, to be published
2009	W. Van Den Daele, S. Cristoloveanu, E. Augendre, C. Le Royer, J. F. Damlencourt, D. Kazazis, A. Zaslavsky	GeOI as a platform for ultimate devices.		FTM	6th Advanced Research Workshop "Future Trends in Microelectronics: Unmapped roadmaps"		Proc. in "Future Trends in Microelectronics : From Nanophotonics to Sensors and Energy", S. Luryi, J. Xu, and A. Zaslavsky eds., Wiley, Hoboken, USA, ISBN 978-0-470-55137-0, pp. 141-158 (2010)
2009	K. Rogdakis, E. Bano, L. Montes, K. Zekentes, M. Bechelany, D. Cornu	Electrical transport properties of catalyst-free grown 3C-SiC nanowires		Hetero-SiC	International workshop on 3C-SiC hetero-epitaxy (Hetero-SiC '09)	Catania, Italy (6-7 May 2009)	
2009	C. M. Mezzomo, M. Marin, C. Leyris, G. Ghibaudo	Mismatch Measure Improvement Using Kelvin Test Structures in Transistor Pair Configuration in Sub-Hundred Nanometer MOSFET Technology		ICMTS	IEEE International Conference on Microelectronic Test Structures	Oxnard, USA (30 March - 2 April 2009)	Proceedings of ICMTS, ISBN 978-1-4244-4259-1, IEEE, pp. 62-67 (2009)
2009	P. Martin, M. Cavalier and G. Ghibaudo	Low-Frequency Noise in a 0.18 $\mu\text{m}$ Mixed-Mode CMOS Technology at Low Temperature		ICNF	International Conference on Noise and Fluctuations (ICNF)	Pisa, Italy (June 2009)	to be published in AIP Conference Proceedings
2009	Y. Xu, T. Minari, K. Tsukagoshi, K. Bock, M. Fadallah, G. Ghibaudo, J.A. Chroboczek	Study of Organic Material FETs by Combined Static and Low Frequency Noise Measurements		ICNF	International Conference on Noise and Fluctuations (ICNF)	Pisa, Italy (June 2009)	AIP Conference Proceedings, Vol. 1129, M. Macucci and G. Basso eds., pp.163-166 (Apr. 2009)
2009	S. Altazin, R. Clerc, R. Gwoziecki, G. Ghibaudo, G. Pananakakis, R. Coppard and C. Serbutoviez	Impact of Ohmic Contacts on Space Charge Limited Currents in Au / Pentacene / Au Structures		ICOE	International Conference on Organic Electronics 2009,	Liverpool, UK (15-17 June 2009)	Sans
2009	K. Rogdakis, E. Bano, L. Montes, M. Bechelany, D. Cornu and K. Zekentes	Field effect transistors based on catalyst-free grown 3C-SiC nanowires		ICSCRM	International Conference on Silicon Carbide and Related Materials	Nuernberg, Germany (Oct. 2009)	Materials Science Forum Vols. 679-680 (2011) pp 613-616

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2009	A. Hubert, E. Nowak, K. Tachi, V. Maffini-Alvaro, C. Vizioz, C. Arvet, J.-P. Colonna, J.-M. Hartmann, V. Loup, L. Baud, S. Pauliac, V. Delaye, C. Carabasse, G. Molas, G. Ghibaudo, B. De Salvo, O. Faynot and T. Ernst	A stacked SONOS technology, up to 4 levels and 6nm crystalline nanowires, with gate-all-around or independent gates ( $\Phi$ -Flash), suitable for full 3D integration.		IEDM	IEEE International Electron Devices Meeting	Baltimore, USA (7-9 Dec. 2009)	IEEE Proceedings of IEDM, pp. 637-640, doi:10.1109/IEDM.2009.5424260 (2009)
2009	G. Bidal, F. Boeur, S. Denorme, C. Laviron, K. Bourdelle, N. Loubet, Y. Campidelli, R. Beneyton, H. Moriceau, F. Fournel, P. Morin, S. Barnola, T. Salvétat, P. Perreau, P. Gouraud, F. Leverd, B. Le-Gratiet, J.L. Huguenin, D. Fleury, K. Kusiaku, A. Cros, C. Leyris, S. Haendler, C. Borowiak, L. Clement, R. Pantel, G. Ghibaudo, and T. Skotnicki	First CMOS Integration of Ultra Thin Body and BOX (UTB2) Structures on Bulk Direct Silicon Bonded (DSB) Wafer with Multi-Surface Orientations		IEDM	IEEE International Electron Devices Meeting	Baltimore, USA (7-9 Dec. 2009)	IEEE Proceedings of IEDM, pp. 677-680, doi:10.1109/IEDM.2009.5424247 (2009)
2009	K. Tachi, M. Casse, D. Jang, C. Dupré, A. Hubert, N. Vulliet, C. Maffini-Alvaro, C. Vizioz, C. Carabasse, V. Delaye, J. M. Hartmann, G. Ghibaudo, H. Iwai, S. Cristoloveanu, O. Faynot and T. Ernst	Relationship between mobility and high-k interface properties in advanced Si and SiGe nanowires		IEDM	IEEE International Electron Devices Meeting	Baltimore, USA (7-9 Dec. 2009)	IEEE Proceedings of IEDM, pp. 313-316, doi:10.1109/IEDM.2009.5424360 (2009)
2009	S. Altazin, R. Clerc, R. Gwoziecki, D. Boudinet, J. M. Verilhac, R. Coppard, G. Ghibaudo, G. Pananakakis, C. Serbutoviez	Vertical Transport in Spin Coated Ultra Thin Polycrystalline Pentacene Organic Stacks		IEDM	IEEE International Electron Devices Meeting	Baltimore, USA (7-9 Dec. 2009)	IEEE Proceedings of IEDM, pp. 387-390, doi:10.1109/IEDM.2009.5424342 (2009)

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2009	X. Xu, B. Bercu, L. Montès	Finite elements study of high mechanical stress in nanostructures for innovative NEMS sensors		IEEE-NEMS	4th IEEE International Conference of Nano/Micro Engineered and Molecular Systems	Shenzhen, China (5-8 Jan. 2009)	IEEE Conference Proceedings NEMS'2011, pp. 676-681, doi:10.1109/NEMS.2009.5068670 (2009)
2009	J. Buckley, I. Pro, R. Barattin, A. Calborean, K. Huang, V. Aiello, G. Nicotra, M. Gely, G. Delapierre, E. Jalaguier, F. Duclairoir, N. Chevalier, D. Mariolle, C. Spinella, S. Lombardo, P. Blaise, P. Maldivi, G. Ghibaudo, R. Baptist and B. De Salvo	From Atomistic to Device Level Investigation of Hybrid Redox Molecular/Silicon Field-Effect Memory Devices		IMW	IEEE International Memory Workshop (ex NVSMW & ICMTD)	Monterey, CA, USA (10-14 May 2009)	to be published (IEEE Conference Proceedings, 2009)
2009	K. Romanjek, E. Augendre, W. Van den Daele, B. Grandchamp, L. Sanchez, C. Le Royer, J.-M. Hertmann, B. Ghyselen, E. Guiot, K. Bourdelle, S. Cristoloveanu, F. Boulanger, I. Clavelier	Improved GeOI substrates for pMOSFET off-state leakage control		INFOS	International Conference on Insulating Films on Semiconductors (INFOS)	Cambridge, UK (29th June - 1st July 2009)	Conference book.
2009	F. Rochette, X. Garros, G. Reibold, F. Andrieu, M. Cassé, M. Mouis, G. Ghibaudo, F. Boulanger	Strain sensitivity of gate leakage in biaxially strained FD-SOI nMOSFETs: a benefit for the performance trade-off and a novel way to extract the strain-induced band offset		INFOS	International Conference on Insulating Films on Semiconductors (INFOS)	Cambridge, UK (29th June - 1st July 2009)	Conference book.
2009	M. Charbonnier, C. Leroux, V. Cosnier, P. Besson, F. Martin, G. Ghibaudo, G. Reibold	Tuning the dipole at the High-k/SiO2 interface in advanced metal gate stacks		INFOS	International Conference on Insulating Films on Semiconductors (INFOS)	Cambridge, UK (29th June - 1st July 2009)	Conference book.
2009	R. Ritzenthaler, F. Lime, O. Faynot, S. Cristoloveanu, B. Iniguez	2D compact modeling of the threshold voltage in triple- and Pi-gate transistors		ISDRS	2009 International Semiconductor Device Research Symposium	Washington DC, USA (9-10 Dec. 2009)	IEEE Conference Proceedings, ISDRS'2009, doi:10.1109/ISDRS.2009.5378333 (2 pages)
2009	E.X. Zhang, D.M. Fleetwood, F.E. Mamouni, M.L. Alles, R.D. Schrimpf, W. Xiong, S. Cristoloveanu	Effects of fin width on memory window in FinFET ZRAMs		ISDRS	2009 International Semiconductor Research Symposium	Washington DC, USA (9-10 Dec. 2009)	IEEE Conference Proceedings, ISDRS'2009, doi: 10.1109/ISDRS.2009.5378208 (2 pages)

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2009	A. Zaka, Q. Rafhay, P. Palestri, R. Clerc, D. Rideau, L. Selmi, C. Tavernier and H. Jaouen	On the Accuracy of Current TCAD Hot Carrier Injection Models for the Simulation of Degradation Phenomena in Nanoscale Devices		ISDRS	2009 International Semiconductor Device Research Symposium	Washington DC, USA (9-10 Dec. 2009)	IEEE Conference Proceeding, ISDRS'2009, doi:10.1109/ISDRS.2009.5378310 (2 pages)
2009	P. Febvre	Digital magnetometers based on the Single-Flux-Quantum technique	Invited paper	ISEC	2nd Superconducting SFQ VLSI Workshop (SSV), satellite of the International Superconductive Electronics Conference (ISEC)	Fukuoka, Japan (16-19 June 2009)	Abstract booklet
2009	C. Buran, M. G. Pala, S. Poli, M. Mouis	Full-3D real-space simulation of surface-roughness effects in double gate MOSFETs		IWCE	13th International Workshop on Computational Electronics (IWCE'2009)	Beijing, China, (27-29 May 2009)	Proceedings of IWCE 2009, IEEE Conference Proceedings CFP09462-PRT, ISBN 978-1-4244-3926-3, pp. 309-312 (2009)
2009	M. Bescond, M. Lannoo, I. Raymond, F. Michelini, M. G. Pala	Influence of ionized impurities in Silicon Nanowire Transistors		IWCE	13th International Workshop on Computational Electronics (IWCE'2009)	Beijing, China, (27-29 May 2009)	Proceedings of IWCE 2009, IEEE Conference Proceedings CFP09462-PRT, ISBN 978-1-4244-3926-3, pp. 137-140 (2009)
2009	G. Ghibaudo, M. Mouis, L. Pham-Nguyen, K. Bennamane, I. Pappas, A. Cros, G. Bidal, D. Fleury, A. Claverie, G. Benassayag, P-F. Fazzini, C. Fenouillet-Beranger, S. Monfray, F. Boeuf, S. Cristoloveanu, T. Skotnicki N. Collaert	Electrical Transport characterization of nano CMOS devices with ultra-thin silicon film.	Invited paper	IWJT	9th International Workshop on Junction Technology (IWJT2009)	Kyoto, Japan (June 2009)	to be published, IEEE Conference Proceedings (2009)
2009	X. Xu, B. Bercu, F. Lime, L. Montès	An innovative NEMS pressure sensor approach based on hetero-nanostructures		MAM	18th Materials For Advanced Metallization Conference	Grenoble (8-11 March 2009)	Abstract booklet, 2 pages. Extended papers submitted to Microelectronic Engineering.
2009	B. Bercu, L. Montes, P. Morfouli	SOI built-in heat spreader with temperature and pressure integrated sensors for cooling optimization and in-situ monitoring		MicroTherm	8th International Conference on Microtechnology and Thermal Problems in Electronics (MicroTherm'2009)	28 juin - 1er juillet 2009, Lodz, Pologne	Sans
2009	Xin Xu, Bogdan Bercu, François Lime, Laurent Montès	The study of mechanical stress in NEMS heterostructures		Nanotech-MEMS & NEMS	NSTI Nanotech 2009, Workshop on MEMS & NEMS	Houston, USA (3-7 May 2009)	Proceedings in Nanotech 2009, Vol. 1, ISBN 978-1-4398-1782-7, pp.476-479 (2009)
2009	P. Martin and G. Ghibaudo	1/f Noise Modeling at Low Temperature with the EKV3 Compact Model.		Nanotech-WCM	NSTI Nanotech 2009, Workshop on Compact Modeling (WCM 2009)	Houston, USA (3-7 May 2009)	Proceedings in Nanotech 2009, Vol. 3, ISBN 978-1-4398-1784-1, pp.636-638 (2009)

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2009	V. Quenette, D. Rideau, R. Clerc, C. Tavernier, H. Jaouen	Dynamic Charge Sharing modeling for surface potential based models		Nanotech-WCM	NSTI Nanotech 2009, Workshop on Compact Modeling (WCM 2009)	Houston, USA, (3-7 May 2009)	Proceedings in Nanotech 2009, Vol. 3, ISBN 978-1-4398-1784-1, pp.558-561 (2009)
2009	D. Garetto, A. Zaka, V. Quenette, D. Rideau, E. Dornel, W. F. Clark, M. Minondo, C. Tavernier, Q. Rafhay, R. Clerc, A. Schmid, Y. Leblebici, and H. Jaouen	Embedded non-volatile memory study with surface potential based model		Nanotech-WCM	NSTI Nanotech 2009, Workshop on Compact Modeling (WCM 2009)	Houston, USA, (3-7 May 2009)	Proceedings in Nanotech 2009, Vol. 3, ISBN 978-1-4398-1784-1, pp.554-557 (2009)
2009	P. Febvre, D. Bouis, and A. Colin	Comparison of Typical Superconducting Structures with Analytical and 3D Modelling Methods		PIERS	Progress In Electromagnetics Research Symposium	August 18-21, Moscow, Russia	
2009	A. Colin and P. Febvre	Design of a Wideband Slot Bow-tie Antenna Excited by a Microstrip to CPW Transition for Applications in the Millimeter Wave Band		PIERS	Progress In Electromagnetics Research Symposium	August 18-21, Moscow, Russia	Proceedings, pp. 1421-1425
2009	G. A. Ardila Rodríguez, H. Durou, A. Ramond, P. Dubreuil, D. Belharet, C. Rossi, D. Esteve	A PZT energy harvester MEMS for low amplitude accelerations: fabrication and characterization		PowerMEMS	9th International Workshop on Micro and Nanotechnology for Power Generation and Energy Conversion Applications	Washington DC, USA, December 1-4, 2009	Proceedings to be published
2009	A. Ramond, G. A. Ardila Rodríguez, H. Durou, B. Jammes, C. Rossi	A SIDO buck converter with ultra low power MPPT scheme		PowerMEMS	9th International Workshop on Micro and Nanotechnology for Power Generation and Energy Conversion Applications	Washington DC, USA (1-4 Dec. 2009)	Proceedings to be published
2009	G. Bidal, D. Fleury, G. Ghibaudo, F. Boeuf and T. Skotnicki	Guidelines for MOSFET Device Optimization accounting for L-dependent Mobility Degradation.		Silicon Nanoelectronics Workshop	Silicon Nanotechnology Workshop	Kyoto, Japan (June 2009)	Sans. Conference workbook.
2009	S. Poli, M.G. Pala	Full quantum investigation of low field mobility in short-channel Silicon nanowire FETs		SISPAD	2009 International Conference on Simulation of Semiconductor Processes and Devices	San Diego, California, USA (9-11 Sept. 2009)	IEEE Conference Proceedings, doi:10.1109/SISPAD.2009.5290193 (4 pages)
2009	E. Augendre, L. Sanchez, J.-M. Hartmann, W. Van des Daele, S. Favier, E. Guiot, B. Ghysselein, K.K. Bourdelle, S. Cristoloveanu, T. Billon, L. Clavelier	Fabrication of Compressively-Strained GeOI Substrates using the Smart Cut™ Technology		SOI Conf	2009 IEEE International SOI Conference	Foster City, California, USA (5-8 Oct. 2009)	2009 IEEE Conference Proceedings, doi:10.1109/SOI.2009.5318768 (2 pages)



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2009	J.-P. Mazellier, J. Widiez, F. Andrieu, M. Lions, S. Saada, M. Hasegawa, K. Tsugawa, L. Brevard, M. Rabarot, V. Delaye, S. Cristoloveanu, L. Clavelier, S. Deleonibus, P. Bergonzo, O. Faynot	First demonstration of heat dissipation improvement in CMOS technology using Silicon-On-Diamond (SOD) substrates		SOI Conf	2009 IEEE International SOI Conference	Foster City, California, USA (5-8 Oct. 2009)	2009 IEEE Conference Proceedings, doi:10.1109/SOI.2009.5318735 (2 pages)
2009	E. Nowak, E. Vianello, L. Perniola, M. Bocquet, G. Molas, R. Kies, M. Gely, G. Ghibaudo, B. De Salvo, G. Reimbold, F. Boulanger	Charge Localization During Program and Retention in NROM-like Nonvolatile Memory Devices.		SSDM	International Conference on Solid State Devices and Materials (SSDM)	Sendai, Japan (6-9 Oct. 2009)	Conference book.
2009	F. Boeuf, G. Ghibaudo and T. Skotnicki	Impact of Coulomb Scattering on the Characteristics of Nanoscale Devices		SSDM	International Conference on Solid State Devices and Materials (SSDM)	Sendai, Japan (6-9 Oct. 2009)	Conference book.
2009	B. Cousin, O. Rozeau, M.-A. Jaud, J. Jomaah	Compact Modeling of Quantization Effects for Cylindrical Gate-All-Around MOSFETs		ULIS	Int. Conference on Ultimate Integration of Silicon	Aachen, Germany (18-20 March 2009)	Proceedings of ULIS 2009, IEEE, pp. 269-272
2009	C. Buran, M. G. Pala, S. Poli, M. Mouis	Full-3D real-space treatment of surface roughness in double gate MOSFETs		ULIS	Int. Conference on Ultimate Integration of Silicon	Aachen, Germany (18-20 March 2009)	Proceedings of ULIS 2009, IEEE, pp. 47-50
2009	E. Buccafurri, R. Clerc, F. Calmon, M. Pala, A. Poncet, and G. Ghibaudo	Intrinsic Cut Off Frequency of Si and GaAs Based Resonant Tunneling Diodes		ULIS	Int. Conference on Ultimate Integration of Silicon	Aachen, Germany (18-20 March 2009)	Proceedings of ULIS 2009, IEEE, pp. 91-94
2009	C. M. Mezzomo, C. Leyris, E. Josse, G. Ghibaudo	Pockets engineering impact on mismatch performance on 45nm MOSFET technologies		ULIS	Int. Conference on Ultimate Integration of Silicon	Aachen, Germany (18-20 March 2009)	Proceedings of ULIS 2009, IEEE, pp. 15-18
2009	N. Rodriguez, F. Gámiz, R. Clerc, C. Sampedro, A. Godoy, G. Ghibaudo	Quantization Effects in Silicided and Metal Gate MOSFETs.		ULIS	Int. Conference on Ultimate Integration of Silicon	Aachen, Germany (18-20 March 2009)	Proceedings of ULIS 2009, IEEE, pp. 103-106
2009	A. Hubert, S. Cristoloveanu, M. Bawedin, T. Ernst	Scalability of MSD memory effect.		ULIS	Int. Conference on Ultimate Integration of Silicon	Aachen, Germany (18-20 March 2009)	Proceedings of ULIS 2009, IEEE, pp. 139-142
2009	K. Bennamane, T. Boutchacha, G. Ghibaudo, M. Mouis, N. Collaert	Static and Low Frequency Noise Characterization of FinFET Devices		ULIS	Int. Conference on Ultimate Integration of Silicon	Aachen, Germany (18-20 March 2009)	Proceedings of ULIS 2009, IEEE, pp. 39-42

Année	Auteurs	Titre		Sigle	Conférence	Lieu, date	Actes
2009	G. Bidal, F. Boeuf, S. Denorme, N. Loubet, J.L.Huguenin, P.Perreau, D.Fleury, F. Leverd, S. Lagrasta, S.Barnola, T.Salvetat, B. Orlando, R. Beneyton, L. Clement, R. Pantel, S. Monfray, G.Ghibaudo and T. Skotnicki	High velocity Si-nanodot : a candidate for SRAM applications at 16nm node and below		VLSI Symposium	IEEE Symposium on VLSI Technology (VLSI Symposium)	Kyoto, Japan (15-17 June 2009)	Proceedings to be published
2009	D. Fleury, G. Bidal, A. Cros, F. Boeuf, T. Skotnicki and G. Ghibaudo	New Experimental Insight into Ballisticity of Transport in Strained Bulk MOSFETs		VLSI Symposium	IEEE Symposium on VLSI Technology (VLSI Symposium)	Kyoto, Japan (15-17 June 2009)	Proceedings to be published
2009	D. Fleury, A. Cros, G. Bidal, H. Brut, E. Josse and G. Ghibaudo	A New Technique to Extract the Gate Bias Dependent S/D Series Resistance of Sub-100nm MOSFETs		VLSI-TSA	International Symposium on VLSI Technology, Systems and Applications (VLSI-TSA)	Hsinchu, Taiwan (27-29 Apr. 2009)	Conference proceedings to be published, IEEE, 2009
2009	B. Cousin, O. Rozeau, M.-A. Jaud, J. Jomaah	A Physics-Based Compact Model of Quantum-Mechanical Effects for Thin Cylindrical Si-Nanowire MOSFETs		VLSI-TSA	International Symposium on VLSI Technology, Systems and Applications (VLSI-TSA)	Hsinchu, Taiwan (27-29 Apr. 2009)	Conference proceedings to be published, IEEE, 2009
2009	M. Collonge, M. Vinet, M. Ribeiro, J.-M. Pedini, B. Previtali, T. Ernst, S. Bécu and G. Ghibaudo	Analytical modeling of accumulation-mode suspended gate MOSFET and process challenges for very low operating power devices.		VLSI-TSA	International Symposium on VLSI Technology, Systems and Applications (VLSI-TSA)	Hsinchu, Taiwan (27-29 Apr. 2009)	Conference proceedings to be published, IEEE, 2009
2009	L. Pham Nguyen, C. Fenouillet-Beranger, P. Perreau, S. Denorme, M.Casse, G. Ghibaudo, T.Skotnicki, S. Cristoloveanu.	Performance Boosters for Advanced SOI CMOS.		WOFE	International Advanced Workshop on 'Frontiers in Electronics' (WOFE 09)	Rincon, Puerto-Rico (12-16 Dec. 2009)	
2009	I. Ionica, J.Champliaud, Y.H. Bae, S. Cristoloveanu	SOI-Pseudo-MOSFET: Platform for high Sensitivity Charge Detection		WOFE	International Advanced Workshop on Frontiers in Electronics (WOFE'09)	Rincon, Puerto-Rico (12-16 Dec. 2009)	Conference Proc., page 11